

WHAT IS CLAIMED IS:

1. A plasma treatment apparatus comprising:
 - a gas supply means for introducing a processing gas into a space between a first electrode and a second electrode under an atmospheric pressure or around atmospheric pressure;
 - a plasma generation means for generating plasma by applying a high frequency voltage to the first electrode or the second electrode under the condition that the processing gas is introduced; and
- 10 a transport means for transporting while floating the object to be treated is transported by floating the object to be treated by blowing the processing gas or a transporting gas to the object to be treated,
 - wherein an etching treatment; an ashing treatment; or a thin film formation is carried out by transferring a relative position of the first electrode and the second electrode, and the object to be treated.
- 15 2. A plasma treatment apparatus according to claim 1, wherein a distance between the object to be treated, and the first electrode and the second electrode are arranged by blowing and sucking the transporting gas simultaneously.
- 20 3. A plasma treatment apparatus according to claim 1, wherein a heating means that heats the processing gas and the transporting gas is provided.
4. A plasma treatment apparatus according to claim 1, wherein the first electrode and the second electrode are separated from an outside by the transport

means.

5. A plasma treatment apparatus according to claim 1, wherein the object to be treated is one selected from a glass substrate; a resin substrate; and a semiconductor
5 substrate.

6. A plasma treatment apparatus according to claim 1, wherein the processing gas is a mixed gas containing a source gas of Si_xH_y and SiH_xCl_y ; one of hydrogen, oxygen, and nitrogen; and a rare gas.

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7. A plasma treatment apparatus according to claim 1, wherein the processing gas is a mixed gas containing a source gas of NF_3 , fluorocarbon, SF_6 , and CO_x ; one of hydrogen and oxygen; and a rare gas.

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8. A plasma treatment apparatus according to claim 1, wherein the processing gas is oxygen, and one of hydrogen, fluorocarbon, NF_3 , H_2O and CHF_3 .

9. A plasma treatment apparatus comprising:

a gas supply means for introducing a processing gas into a space between a
20 first electrode and a second electrode under an atmospheric pressure or around atmospheric pressure ;

a plasma generation means for generating plasma by applying a high frequency voltage to the first electrode or the second electrode under the condition that the processing gas is introduced; and

25 a transport means for transporting while floating the object to be treated is

transported by floating an object to be treated by blowing the processing gas or a transporting gas to the object to be treated,

wherein a cleaning treatment of a component is carried out by using the first electrode and the second electrode.

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10. A plasma treatment apparatus according to claim 9, wherein a distance between the object to be treated, and the first electrode and the second electrode are arranged by blowing and sucking the transporting gas simultaneously.

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11. A plasma treatment apparatus according to claim 9, wherein a heating means that heats the processing gas and the transporting gas is provided.

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12. A plasma treatment apparatus according to claim 9, wherein the first electrode and the second electrode are separated from an outside by the transport means.

13. A plasma treatment apparatus according to claim 9, wherein the object to be treated is one selected from a glass substrate; a resin substrate; and a semiconductor substrate.

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14. A plasma treatment apparatus according to claim 9, wherein the processing gas is a mixed gas containing a source gas of Si_xH_y and SiH_xCl_y ; one of hydrogen, oxygen, and nitrogen; and a rare gas.

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15. A plasma treatment apparatus according to claim 9, wherein the processing

gas is a mixed gas containing a source gas of NF₃, fluorocarbon, SF₆, and CO_x; one of hydrogen and oxygen; and a rare gas.

16. A plasma treatment apparatus according to claim 9, wherein the processing
5 gas is oxygen, and one of hydrogen, fluorocarbon, NF₃, H₂O and CHF₃.

17. A plasma treatment apparatus comprising:
a gas supply means for introducing a processing gas into a space between a first electrode and a second electrode under an atmospheric pressure or around
10 atmospheric pressure;
a plasma generation means for generating plasma by applying a high frequency voltage to the first electrode or the second electrode under the condition that the processing gas is introduced; and
a transport means for transporting while floating an object to be treated is transported by floating the object to be treated by blowing the processing gas or a transporting gas to the object to be treated,
wherein an etching treatment; an ashing treatment; or a thin film formation is carried out by transferring a relative position of the first electrode and the second electrode, and the object to be treated, and
20 wherein the first electrode is formed surrounding the periphery of the second electrode, and formed in a cylindrical shape having the gas supply port of a nozzle shape at its edge.

18. A plasma treatment apparatus according to claim 17, wherein a distance
25 between the object to be treated, and the first electrode and the second electrode are

arranged by blowing and sucking the transporting gas simultaneously.

19. A plasma treatment apparatus according to claim 17, wherein a heating means that heats the processing gas and the transporting gas is provided.

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20. A plasma treatment apparatus according to claim 17, wherein the first electrode and the second electrode are separated from an outside by the transport means.

10 21. A plasma treatment apparatus according to claim 17, wherein the object to be treated is one selected from a glass substrate; a resin substrate; and a semiconductor substrate.

15 22. A plasma treatment apparatus according to claim 17, wherein the processing gas is a mixed gas containing a source gas of Si_xH_y and SiH_xCl_y ; one of hydrogen, oxygen, and nitrogen; and a rare gas.

20 23. A plasma treatment apparatus according to claim 17, wherein the processing gas is a mixed gas containing a source gas of NF_3 , fluorocarbon, SF_6 , and CO_x ; one of hydrogen and oxygen; and a rare gas.

24. A plasma treatment apparatus according to claim 17, wherein the processing gas is oxygen, and one of hydrogen, fluorocarbon, NF_3 , H_2O and CHF_3 .

25 25. A plasma treatment apparatus comprising:

a gas supply means for introducing a processing gas into a space between a first electrode and a second electrode under an atmospheric pressure or around atmospheric pressure ;

5 a plasma generation means for generating plasma by applying a high frequency voltage to the first electrode or the second electrode under the condition that the processing gas is introduced; and

a transport means for transporting while floating an object to be treated is transported by floating an object to be treated by blowing the processing gas or a transporting gas to the object to be treated,

10 wherein a cleaning treatment of a component is carried out by using the first electrode and the second electrode, and

wherein the first electrode is formed surrounding the periphery of the second electrode, and formed in a cylindrical shape having the gas supply port of a nozzle shape at its edge.

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26. A plasma treatment apparatus according to claim 25, wherein a distance between the object to be treated, and the first electrode and the second electrode are arranged by blowing and sucking the transporting gas simultaneously.

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27. A plasma treatment apparatus according to claim 25, wherein a heating means that heats the processing gas and the transporting gas is provided.

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28. A plasma treatment apparatus according to claim 25, wherein the first electrode and the second electrode are separated from an outside by the transport means.

29. A plasma treatment apparatus according to claim 25, wherein the object to be treated is one selected from a glass substrate, a resin substrate and a semiconductor substrate.

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30. A plasma treatment apparatus according to claim 25, wherein the processing gas is a mixed gas containing a source gas of Si_xH_y and SiH_xCl_y ; one of hydrogen, oxygen, and nitrogen; and a rare gas.

10 31. A plasma treatment apparatus according to claim 25, wherein the processing gas is a mixed gas containing a source gas of NF_3 , fluorocarbon, SF_6 , and CO_x ; one of hydrogen and oxygen; and a rare gas.

15 32. A plasma treatment apparatus according to claim 25, wherein the processing gas is oxygen, and one of hydrogen, fluorocarbon, NF_3 , H_2O and CHF_3 .

33. A method for plasma treatment comprising the steps of:
introducing a processing gas into a space between a first electrode and a second electrode under an atmospheric pressure or around atmospheric pressure ;
20 generating plasma by applying a high frequency voltage to the first electrode or the second electrode under the condition that the processing gas is introduced; and
transferring an object to be treated with being floated by blowing the processing gas or a transporting gas to a substrate to be treated,
wherein an ashing treatment; or a thin film formation is carried out by
25 transferring a relative position of the first electrode and the second electrode, and the

object to be treated.

34. A method for plasma treatment comprising the steps of:
- introducing a processing gas into a space between a first electrode and a
- 5 second electrode under an atmospheric pressure or around atmospheric pressure;
- generating plasma by applying a high frequency voltage to the first electrode
- or the second electrode under the condition that the processing gas is introduced; and
- transferring an object to be treated with being floated by blowing the
- processing gas or a transporting gas to the object to be treated,
- 10 wherein a cleaning treatment of a component is carried out by the first
- electrode and the second electrode.

35. A method for manufacturing a thin film transistor, comprising the steps of:
- forming a gate electrode over a substrate having a insulating surface;
- 15 forming a gate insulating film over the substrate;
- forming an amorphous semiconductor film over the gate insulating film;
- forming a crystalline semiconductor film by crystallizing the amorphous
- semiconductor film; and
- forming a insulating film over the crystalline semiconductor film,
- 20 wherein a processing gas is introduced into a space between a first electrode
- and a second electrode of a plasma apparatus under an atmospheric pressure or
- around atmospheric pressure for generating plasma by applying a high frequency
- voltage to the first electrode or the second electrode.

- 25 36. A method for manufacturing a thin film transistor, comprising the steps of:

forming a gate electrode over a substrate having a insulating surface;

forming a gate insulating film over the substrate;

forming an amorphous semiconductor film over the gate insulating film; and

forming a insulating film over the amorphous semiconductor film,

5 wherein a processing gas is introduced into a space between a first electrode and a second electrode of a plasma apparatus under an atmospheric pressure or around atmospheric pressure for generating plasma by applying a high frequency voltage to the first electrode or the second electrode.